



3N70

Power MOSFET

3 AMPS, 700 VOLTS N-CHANNEL POWER MOSFET

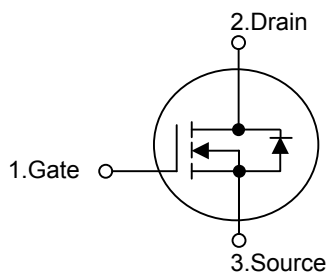
■ DESCRIPTION

The UTC **3N70** is a high voltage and high current power MOSFET , designed to have better characteristics, such as fast switching time, low gate charge, low on-state resistance and have a high rugged avalanche characteristics. This power MOSFET is usually used at high speed switching applications in power supplies, PWM motor controls, high efficient DC to DC converters and bridge circuits.

■ FEATURES

- * $R_{DS(ON)} \leq 4.0\Omega$ @ $V_{GS} = 10V$
- * Ultra low gate charge (typical 10 nC)
- * Low reverse transfer capacitance
- * Fast switching capability
- * Avalanche energy specified
- * Improved dv/dt capability, high ruggedness

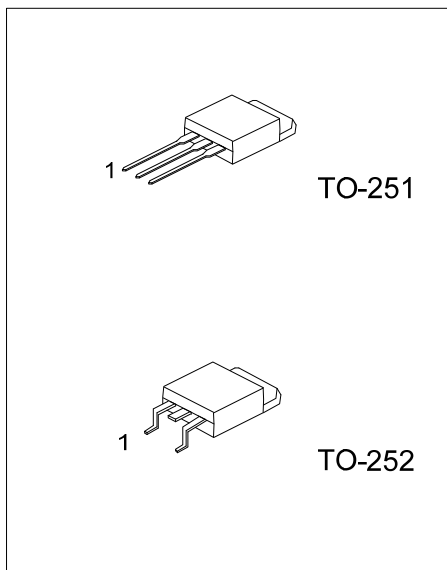
■ SYMBOL



■ ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
3N70L-TM3-T	3N70G-TM3-T	TO-251	G	D	S	Tube
3N70L-TN3-R	3N70G-TN3-R	TO-252	G	D	S	Tape Reel

<p>3N70L-TM3-T</p> <p>(1)Packing Type (2)Package Type (3)Lead Plating</p>	<p>(1) R: Tape Reel, T: Tube (2) TM3: TO-251, TN3: TO-252 (3) G: Halogen Free, L: Lead Free</p>
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■ ABSOLUTE MAXIMUM RATINGS ($T_C = 25^\circ\text{C}$, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V_{DSS}	700	V
Gate-Source Voltage		V_{GSS}	± 30	V
Avalanche Current (Note 2)		I_{AR}	3.0	A
Continuous Drain Current		I_D	3.0	A
Pulsed Drain Current (Note 2)		I_{DM}	12	A
Avalanche Energy	Single Pulsed (Note 3)	E_{AS}	200	mJ
	Repetitive (Note 2)	E_{AR}	7.5	mJ
Peak Diode Recovery dv/dt (Note 4)		dv/dt	4.5	V/ns
Power Dissipation		P_D	50	W
Junction Temperature		T_J	+150	$^\circ\text{C}$
Operating Temperature		T_{OPR}	-55 ~ +150	$^\circ\text{C}$
Storage Temperature		T_{STG}	-55 ~ +150	$^\circ\text{C}$

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Repetitive Rating: Pulse width limited by maximum junction temperature

3. $L = 64\text{mH}$, $I_{AS} = 2.4\text{A}$, $V_{DD} = 50\text{V}$, $R_G = 25 \Omega$, Starting $T_J = 25^\circ\text{C}$

4. $I_{SD} \leq 3.0\text{A}$, $di/dt \leq 200\text{A}/\mu\text{s}$, $V_{DD} \leq BV_{DSS}$, Starting $T_J = 25^\circ\text{C}$

■ THERMAL DATA

PARAMETER	SYMBOL	RATING	UNIT
Junction to Ambient	θ_{JA}	110	$^\circ\text{C}/\text{W}$
Junction to Case	θ_{JC}	2.5	$^\circ\text{C}/\text{W}$

■ ELECTRICAL CHARACTERISTICS ($T_C = 25^\circ\text{C}$, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS} = 0\text{V}$, $I_D = 250\mu\text{A}$	700			V
Drain-Source Leakage Current	I_{DSS}	$V_{DS} = 700\text{V}$, $V_{GS} = 0\text{V}$			10	μA
Gate-Source Leakage Current	Forward	I_{GSS}			100	nA
	Reverse				-100	nA
Breakdown Voltage Temperature Coefficient	$\Delta BV_{DSS}/\Delta T_J$	$I_D = 250\mu\text{A}$, Referenced to 25°C		0.6		$\text{V}/^\circ\text{C}$
ON CHARACTERISTICS						
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{DS} = V_{GS}$, $I_D = 250\mu\text{A}$	2.0		4.0	V
Static Drain-Source On-State Resistance	$R_{DS(ON)}$	$V_{GS} = 10\text{V}$, $I_D = 1.5\text{A}$		2.8	4.0	Ω
DYNAMIC CHARACTERISTICS						
Input Capacitance	C_{ISS}	$V_{DS} = 25\text{V}$, $V_{GS} = 0\text{V}$, $f = 1\text{MHz}$		350	450	pF
Output Capacitance	C_{OSS}		50	65	pF	
Reverse Transfer Capacitance	C_{RSS}		5.5	32	pF	
SWITCHING CHARACTERISTICS						
Turn-On Delay Time	$t_{D(ON)}$	$V_{DD} = 30\text{V}$, $I_D = 1.0\text{A}$, $R_G = 25\Omega$ (Note 1, 2)		10	40	ns
Turn-On Rise Time	t_R		30	70	ns	
Turn-Off Delay Time	$t_{D(OFF)}$		20	100	ns	
Turn-Off Fall Time	t_F		30	70	ns	
Total Gate Charge	Q_G		$V_{DS} = 480\text{V}$, $I_D = 3.0\text{A}$, $V_{GS} = 10\text{V}$ (Note 1, 2)		10	13
Gate-Source Charge	Q_{GS}	2.7			nC	
Gate-Drain Charge	Q_{DD}	4.9			nC	

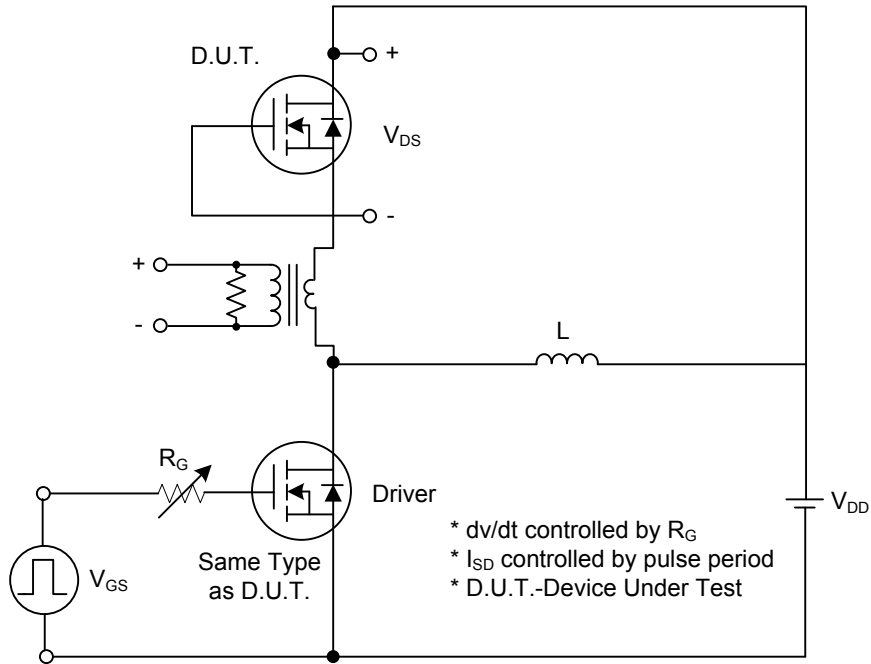
■ ELECTRICAL CHARACTERISTICS(Cont.)

SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS					
Drain-Source Diode Forward Voltage	V_{SD}	$V_{GS} = 0 \text{ V}, I_S = 3.0 \text{ A}$		1.4	V
Maximum Continuous Drain-Source Diode Forward Current	I_S			3.0	A
Maximum Pulsed Drain-Source Diode Forward Current	I_{SM}			12	A
Reverse Recovery Time	t_{RR}	$V_{GS} = 0 \text{ V}, I_S = 3.0 \text{ A},$ $di_F/dt = 100 \text{ A}/\mu\text{s}$ (Note 1)		210	ns
Reverse Recovery Charge	Q_{RR}			1.2	μC

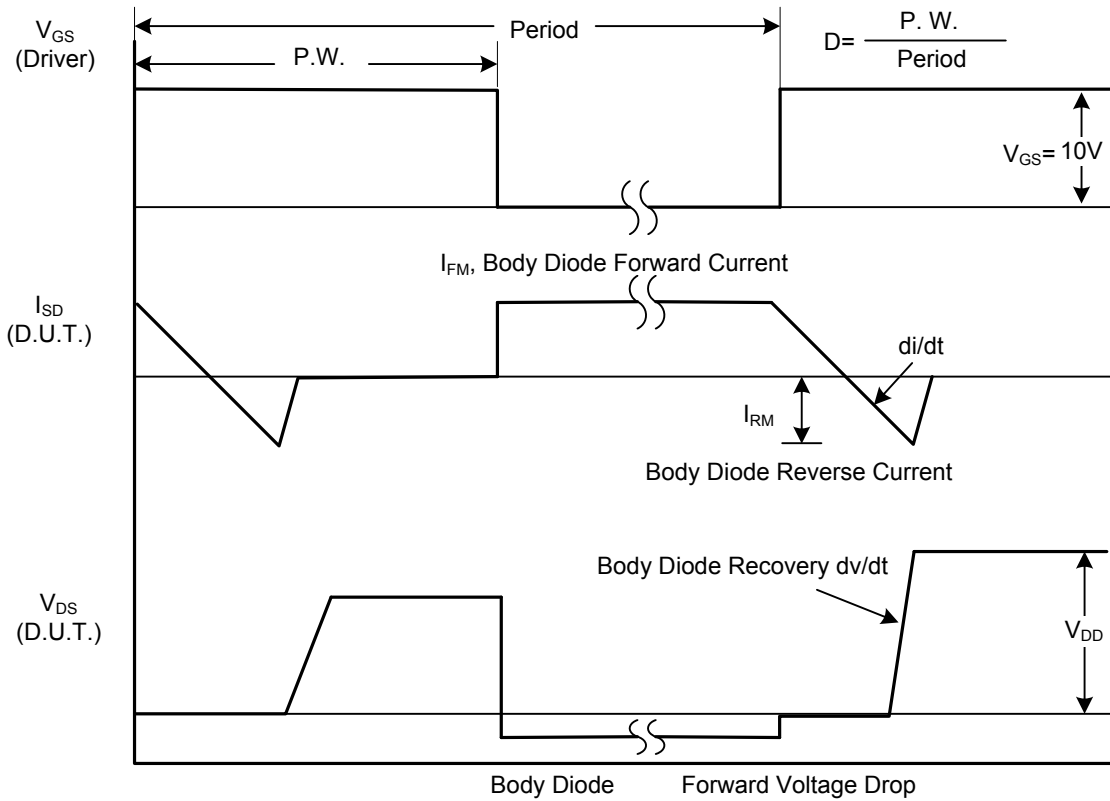
Notes: 1. Pulse Test: Pulse width $\leq 300\mu\text{s}$, Duty cycle $\leq 2\%$

2. Essentially independent of operating temperature

■ TEST CIRCUITS AND WAVEFORMS

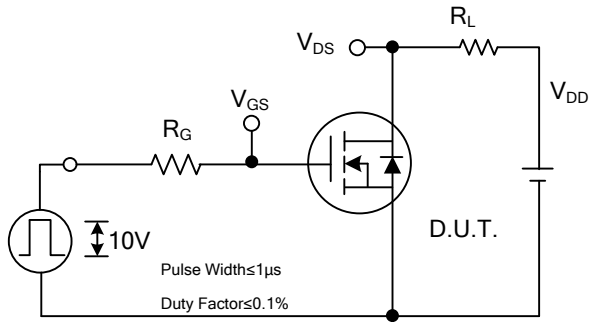


1A Peak Diode Recovery dv/dt Test Circuit

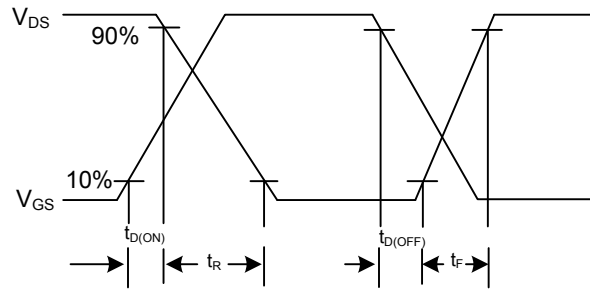


1B Peak Diode Recovery dv/dt Waveforms

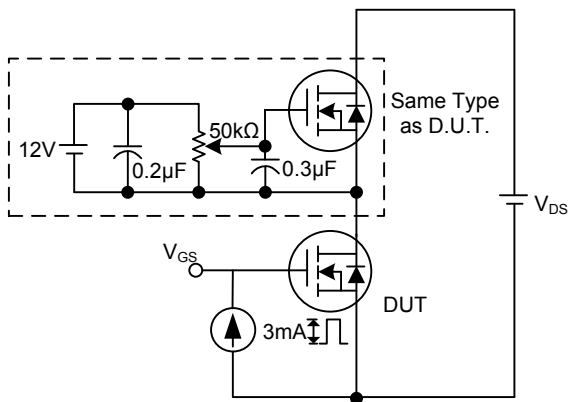
■ TEST CIRCUITS AND WAVEFORMS (Cont.)



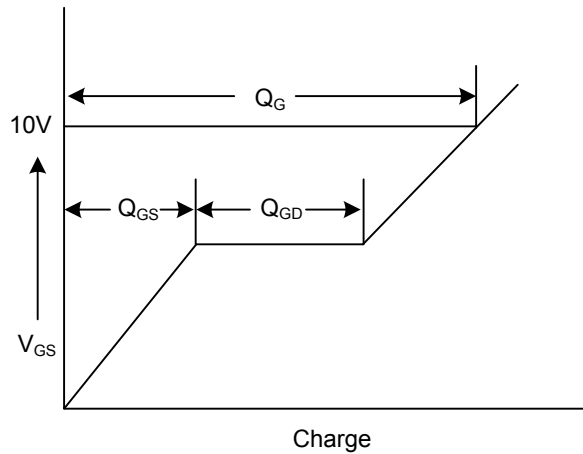
2A Switching Test Circuit



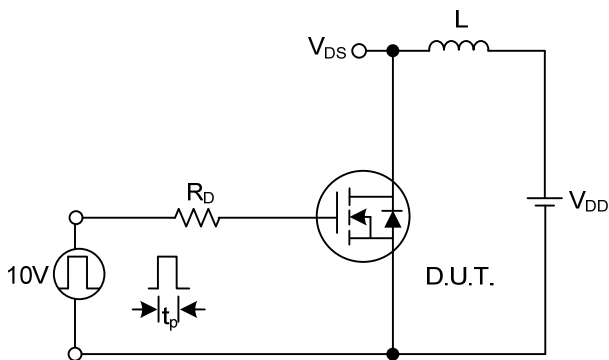
2B Switching Waveforms



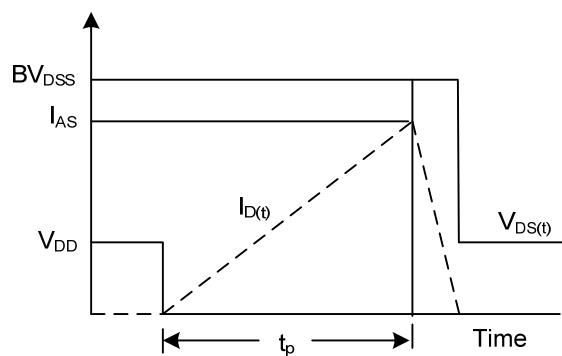
3A Gate Charge Test Circuit



3B Gate Charge Waveform

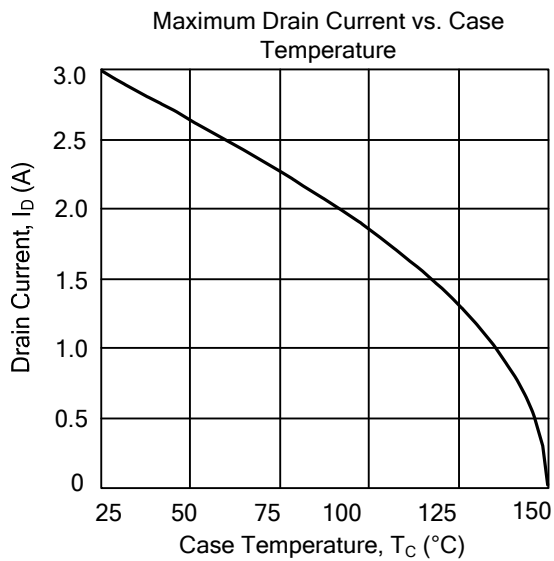
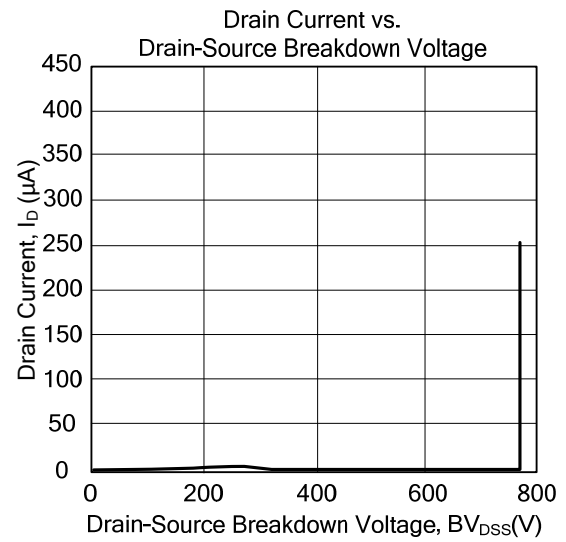
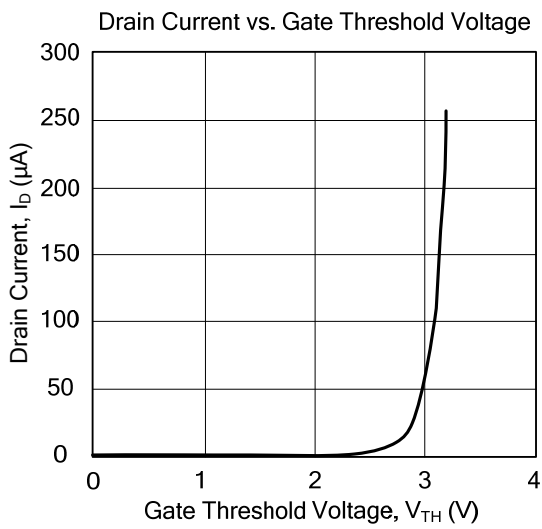
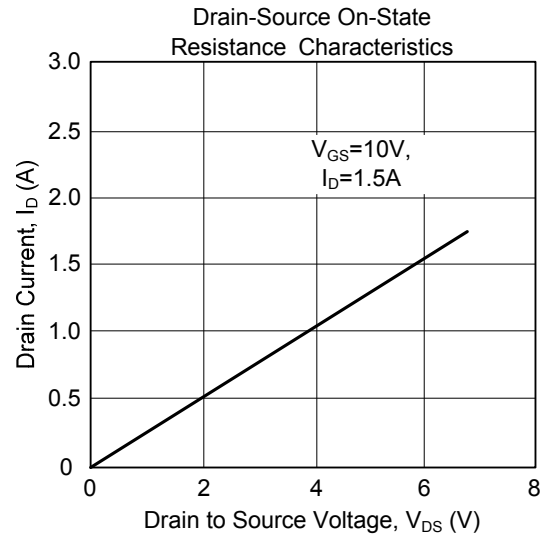
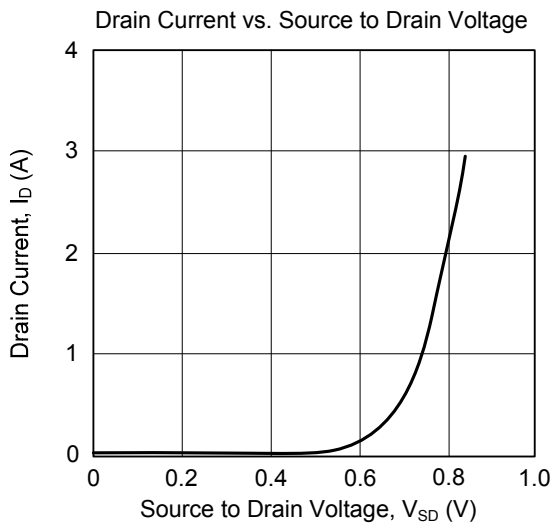


4A Unclamped Inductive Switching Test Circuit



4B Unclamped Inductive Switching Waveforms

TYPICAL CHARACTERISTICS



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